Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L11	1	'two gate electrode' and undoped near oxide and ('subatmospheric-chemical vapor deposited 'SA-C10/919555 and 10/954400D') near ('BPSG' 'boron and phosporous-doped silicon oxide) and gap.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/01 14:42

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S71	5	("6080639").URPN.	USPAT	OR	OFF	2005/11/01 13:05
S72	13	("5182221" | "6030881" | "6080639" | "6261957" | "6297128" | "6306722" | "6319796" | "6323102" | "6329261" | "6376391" | "6410446" | "6432797" | "6531377").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/11/01 13:13
S73	13	("5182221" | "6030881" | "6080639" | "6261957" | "6297128" | "6306722" | "6319796" | "6323102" | "6329261" | "6376391" | "6410446" | "6432797" | "6531377").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/11/01 13:16
S74	4	("5621241" | "5679606" | "5716890" | "5968610").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/11/01 13:22
S78	7718	(257/295,298,314-326).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/01 14:45
S79	995	(floating adj gate) with dielectric with (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/01 14:50
S80	19358	BPSG PBSG (phosphorous near boron near (silicate silicon adj oxide) near glass)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/01 14:49
S81	2	S79 with S80	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/01 14:51
S82	2766	(floating adj gate) and dielectric with (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/01 14:50
S83	426	S82 and S80	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/01 14:50

S84	11	S79 same S80	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/01 14:56